HIGH-SPEED 3.3V 8/4K x 18 IDT70V9359/49L SYNCHRONOUS PIPELINED OBSOLETE PARTS **DUAL-PORT STATIC RAM**

LEAD FINISH (SnPb) ARE IN EOL PROCESS - LAST TIME BUY EXPIRES JUNE 15, 2018

Features:

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed clock to data access
 - Commercial: 6.5/7.5/9ns (max.)
 - Industrial: 7.5ns (max.)
- Low-power operation
 - IDT70V9359/49L Active: 450mW (typ.) Standby: 1.5mW (tvp.)
- Flow-Through or Pipelined output mode on either port via the FT/PIPE pins
- Counter enable and reset features
- Dual chip enables allow for depth expansion without additional logic

- ٠ Full synchronous operation on both ports
 - 3.5ns setup to clock and Ons hold on all control, data, and address inputs
 - Data input, address, and control registers
 - Fast 6.5ns clock to data out in the Pipelined output mode

 - Self-timed write allows fast cycle time
 10ns cycle time, 100MHz operation in Pipelined output mode
- Separate upper-byte and lower-byte controls for multiplexed bus and bus matching compatibility
- LVTTL-compatible, single 3.3V (±0.3V) power supply
- Industrial temperature range (-40°C to +85°C) is available for 83 MHz
- Available in a 100-pin Thin Quad Flatpack (TQFP) and 100pin Fine Pitch Ball Grid Array (fpBGA) packages Green parts available, see ordering information



5638 drw 01

NOTE

1. A12 is a NC for IDT70V9349.

High-Speed 3.3V 8/4K x 18 Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

Description:

The IDT70V9359/49 is a high-speed 8/4K x 18 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT70V9359/49 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by \overline{CE}_0 and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode. Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 450mW of power.

PinConfigurations^(1,2,3,4)



- 1. A12 is a NC for IDT70V9349.
- 2. All VDD pins must be connected to power supply.
- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 14mm x 14mm x 1.4mm.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

PinConfigurations(cont'd)^(1,2,3,4)

07/03/02

70V9359/49BF BF100⁽⁵⁾

100-Pin fpBGA Top View⁽⁶⁾

07/03/02									
A1	A2		Α4	^{A5}	A6	^{A7}	a8	a9	a10
A8R	A11R		CNTRSTR	Vss	Vss	Vss	I/O13R	I/O10r	I/O17R
B1	B2	B3	B4	^{B5}	-	³⁷	b8	b9	b10
A6R	A7R	A10R	A12R ⁽¹⁾	R∕₩r		PL/FTr	I/O12R	I/O9r	I/O6R
C1	C2	C3	C4	C5	C6	C7	C8	C9	С10
A3R	A 4R	A5R	A 9R	CE1R	I/O16R	I/O15R	I/O11R	I/O7R	I/Озп
D1	D2	D3	D4	D5	D6	D7	d8	d9	D10
Aor	CLKR	A1R	A 2R	LBR	CE0R	I/O14R	I/O8r	I/O5r	I/O1R
E1	e2	E3	E4	e5	^{E6}	e7	e8	e9	E10
Vss	ADSr	CNTEN _R	A1L	ADSl	Vss	I/O4r	I/O2r	I/Oor	VDD
F1	F2	F3	F4	F5	^{F6}	f7	f8	F9	F10
Vss	CLKL	Aol	A3L	Vdd	Vss	Vdd	I/O2l	I/O1L	I/Ool
G1	G2	G3	G4	G5	G6	G7	G8	^{G9}	G10
CNTEN∟	A4L	A7L	UBL	Vss	I/O13L	NC	I/O4L	Vss	I/O3L
H1 A2L	H2 A6L	H3 A11L		H5 CNTRST∟	h6 I/O15l		h8 I/O7l	H9 I/O6L	н10 I/O5L
J1	J2	J3	^{J4}	J5	^{j6}	J7	J8	^{J9}	J10
A5L	A9L	A12L ⁽¹⁾	R/₩L	OEL	PL∕ FT ∟	I/O12L	I∕O10L	Vss	I/O8∟
K1	K2	K3	K4	K5	K6	к7	к8	к9	к10
A8L	A10L	LBL	CE1∟	Vdd	Vdd	I/O16L	I/O14L	I/O11L	I/O17L

5638 drw 03

NOTES:

1. A12 is a NC for IDT70V9349.

- 2. All VDD pins must be connected to power supply.
- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 10mm x 10mm x 1.4mm with 0.8mm ball pitch.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

High-Speed 3.3V 8/4K x 18 Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

Pin Names

Left Port	Right Port	Names
CE0L, CE1L	CEOR, CE1R	Chip Enables ⁽³⁾
R/WL	R/WR	Read/Write Enable
OEL	0E r	Output Enable
Aol - A12L ⁽¹⁾	Aor - A12r ⁽¹⁾	Address
1/Ool - 1/017l	I/Oor - I/O17R	Data Input/Output
CLKL	CLKR	Clock
ŪBL	UB R	Upper Byte Select ⁽²⁾
LB L	LB R	Lower Byte Select ⁽²⁾
ADSL	ADSR	Address Strobe Enable
	CNTEN R	Counter Enable
CNTRSTL	CNTRST R	Counter Reset
FT/PIPEL	FT/PIPER	Flow-Through / Pipeline
V	DD	Power (3.3V)
V	SS	Ground (0V)

NOTE:

- A12 is a NC for IDT70V9349.
 IB and UB are single buffered regardless of state of FT/PIPE.
- 3. $\overline{\text{CE}}$ o and CE1 are single buffered when $\overline{\text{FT}}/\text{PIPE} = V_{\text{IL}}$, \overline{CE} o and CE1 are double buffered when \overline{FT} /PIPE = VIH,
- i.e. the signals take two cycles to deselect.

Truth Table I—Read/Write and Enable Control^(1,2,3)

ŌĒ	CLK	<u>₹</u> €0 ⁽⁵⁾	CE1 ⁽⁵⁾	UB ⁽⁴⁾	LB ⁽⁴⁾	R/W	Upper Byte I/O9-17	Lower Byte I/O ₀₋₈	MODE
Х	Ŷ	Н	Х	Х	Х	Х	High-Z	High-Z	Deselected-Power Down
Х	Ŷ	Х	L	Х	Х	Х	High-Z	High-Z	Deselected-Power Down
Х	Ŷ	L	Н	Н	Н	Х	High-Z	High-Z	Both Bytes Deselected
Х	Ŷ	L	Н	L	Н	L	DATAin	High-Z	Write to Upper Byte Only
Х	Ŷ	L	Н	Н	L	L	High-Z	DATAN	Write to Lower Byte Only
Х	Ŷ	L	Н	L	L	L	DATAin	DATAN	Write to Both Bytes
L	↑	L	Н	L	Н	Н	DATAOUT	High-Z	Read Upper Byte Only
L	Ŷ	L	Н	Н	L	Н	High-Z	DATAOUT	Read Lower Byte Only
L	Ŷ	L	Н	L	L	Н	DATAOUT	DATAout	Read Both Bytes
Н	Х	L	Н	Х	Х	Х	High-Z	High-Z	Outputs Disabled

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. \overline{ADS} , \overline{CNTEN} , $\overline{CNTRST} = X$.

OE is an asynchronous input signal.
 LB and UB are single buffered regardless of state of FT/PIPE.

5. CEo and CE1 are single buffered when FT/PIPE = VIL. CEo and CE1 are double buffered when FT/PIPE = VIH, i.e. the signals take two cycles to deselect.

5638 tbl 02

⁵⁶³⁸ tbl 01

IDT70V9359/49L High-Speed 3.3V 8/4K x 18 Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

5638 tbl 03

5638 tbl 05

5638 tbl 07

Truth Table II—Address Counter Control^(1,2)

External Address	Previous Internal Address	Internal Address Used	CLK	ADS	CNTEN	CNTRST	I/O ⁽³⁾	MODE
An	Х	An	\uparrow	L ⁽⁴⁾	Х	Н	Dvo (n)	External Address Used
Х	An	An + 1	Ŷ	Н	L ⁽⁵⁾	Н	Dvo(n+1)	Counter Enabled—Internal Address generation
Х	An + 1	An + 1	Ŷ	Н	Н	Н	Dvo(n+1)	External Address Blocked—Counter disabled (An + 1 reused)
Х	Х	A0	Ŷ	Х	Х	L ⁽⁴⁾	Dvo(0)	Counter Reset to Address 0

NOTES:

3. Outputs configured in Flow-Through Output mode: if outputs are in Pipelined mode the data out will be delayed by one cycle.

4. ADS and CNTRST are independent of all other signals including CE0, CE1, UB and LB.

5. The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other signals including CE0, CE1, UB and LB.

Recommended Operating Temperature and Supply Voltage

Grade	Ambient Temperature ⁽¹⁾	GND	Vdd
Commercial	$0^{\circ}C$ to $+70^{\circ}C$	0V	3.3V <u>+</u> 0.3V
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3V
			5638 tbl 04

NOTES:

1. This is the parameter TA. This is the "instant on" case temperature.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Мах.	Unit
Vdd	Supply Voltage	3.0	3.3	3.6	V
Vss	Ground	0	0	0	V
Vih	Input High Voltage	2.0	_	VDD+0.3V ⁽²⁾	V
VIL	Input Low Voltage	-0.3 ⁽¹⁾		0.8	V

NOTES:

1. $V_{IL} > -1.5V$ for pulse width less than 10 ns.

2. VTERM must not exceed VDD+0.3V.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
Tbias	Temperature Under Bias	-55 to +125	٥C
Tstg	Storage Temperature	-65 to +150	٥C
Іоит	DC Output Current	50	mA
			5638 tbl 06

NOTES:

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

2. VTERM must not exceed VDD +0.3V for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq VDD + 0.3V.

Capacitance⁽¹⁾ $(TA = +25^{\circ}C, f = 1.0MHz)$

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
Cin	Input Capacitance	VIN = 3dV	9	рF
Cout ⁽³⁾	Output Capacitance	Vout = 3dV	10	pF

NOTES:

1. These parameters are determined by device characterization, but are not production tested.

2. 3dV references the interpolated capacitance when the input and output switch from OV to 3V or from 3V to 0V.

3. COUT also references CI/O

Industrial and Commercial Temperature Ranges

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (V_{DD} = 3.3V ± 0.3V)

			70V93	59/49L	
Symbol	Parameter	Test Conditions	Min.	Мах.	Unit
LL	Input Leakage Current ⁽¹⁾	$V_{DD} = 3.6V$, $V_{IN} = 0V$ to V_{DD}		5	μA
Ilo	Output Leakage Current	\overline{CE} = VIH or CE1 = VIL, Vout = 0V to VDD		5	μA
Vol	Output Low Voltage	IoL = +4mA		0.4	V
Vон	Output High Voltage	IOH = -4mA	2.4		V

NOTE:

1. At VDD \leq 2.0V input leakages are undefined.

DC Electrical Characteristics Over the Operating Temperature Supply Voltage Range⁽³⁾ ($V_{DD} = 3.3V \pm 0.3V$)

				Version		59/49L6 I Only	70V9359/49L7 Com'l & Ind		70V9359/49L9 Com'l Only		
Symbol	Parameter	Test Condition	Versio			Мах.	Тур. ⁽⁴⁾	Мах.	Тур. ⁽⁴⁾	Max.	Unit
lod	Dynamic Operating Current (Both			L	175	330	155	280	135	230	mA
	Ports Active)	Outputs Disabled, $f = fMAX^{(1)}$	IND	L			155	330	_		
ISB1	Standby Current	$\overline{CE}L = \overline{CE}R = VIH$	COM'L	L	50	80	40	70	30	60	mA
	(Both Ports - TTL Level Inputs)	$f = fMAX^{(1)}$	IND	L			40	80			
ISB2	Standby	$\frac{\overline{CE}}{\overline{CE}} A^{"} = VIL \text{ and } $	COM'L	L	115	185	105	170	95	155	mA
	Current (One Port - TTL Level Inputs)	Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	L			105	180			
ISB3	Full Standby	Both Ports CEL and	COM'L	L	0.5	3.0	0.5	3.0	0.5	3.0	mA
	Current (Both Ports - CMOS Level Inputs)		IND	L			0.5	3.0			
ISB4	Full Standby	\overline{CE} "A" $\leq 0.2V$ and	COM'L	L	105	175	95	160	85	145	mA
	Current (One Port - CMOS Level Inputs)	$\begin{array}{l} \overline{\text{CE}"}\text{B"} & \geq \text{V}_{\text{DD}} - 0.2\text{V}^{(5)} \\ \overline{\text{V}}\text{N} & \geq \text{V}_{\text{DD}} - 0.2\text{V or} \\ \overline{\text{V}}\text{N} & \leq 0.2\text{V}, \text{ Active Port,} \\ Outputs Disabled, f = fMAX^{(1)} \end{array}$	IND	L			95	175		_	

NOTES:

1. At f = fMAX, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.

2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.

3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

4. VDD = 3.3V, TA = 25°C for Typ, and are not production tested. Icc Dc(f=0) = 90mA (Typ).

5. $\overline{CE}x = VIL$ means $\overline{CE}ox = VIL$ and CE1x = VIH

 $\overline{CE}x = VIH \text{ means } \overline{CE}OX = VIH \text{ or } CE1X = VIL$

 $\overline{\text{CE}}\text{x} \leq 0.2 \text{V}$ means $\overline{\text{CE}}\text{ox} \leq 0.2 \text{V}$ and $\text{CE}\text{1x} \geq \text{V}\text{DD}$ - 0.2 V

 $\overline{\text{CEx}} \ge V_{\text{DD}} - 0.2V \text{ means } \overline{\overline{\text{CE}}}_{\text{OX}} \ge V_{\text{DD}} - 0.2V \text{ or } \text{CE}_{1X} \le 0.2V$

"X" represents "L" for left port or "R" for right port.

6

5638 tbl 08

5638 tbl 09

High-Speed 3.3V 8/4K x 18 Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

AC Test Conditions

Input Pulse Levels	GND to 3.0V				
Input Rise/Fall Times	2ns Max.				
Input Timing Reference Levels	1.5V				
Output Reference Levels	1.5V				
Output Load	Figures 1, 2, and 3				

5638 tbl 10





Figure 1. AC Output Test load.



Figure 2. Output Test Load (For tcklz, tcklz, tolz, and tolz). *Including scope and jig.



Figure 3. Typical Output Derating (Lumped Capacitive Load).

High-Speed 3.3V 8/4K x 18 Dual-Port Synchronous Pipelined Static RAM

AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing)⁽³⁾ ($V_{DD= 3.3V \pm 0.3V}$)

			59/49L6 I Only	70V9359/49L7 Com'l & Ind		70V9359/49L9 Com'l Only		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
tcyc1	Clock Cycle Time (Flow-Through) ⁽²⁾	19		22		25	—	ns
tcyc2	Clock Cycle Time (Pipelined) ⁽²⁾	10		12		15	_	ns
tcн1	Clock High Time (Flow-Through) ⁽²⁾	6.5		7.5		12	—	ns
tal1	Clock Low Time (Flow-Through) ⁽²⁾	6.5		7.5		12	—	ns
tCH2	Clock High Time (Pipelined) ⁽²⁾	4		5		6	—	ns
tal2	Clock Low Time (Pipelined) ⁽²⁾	4		5		6	—	ns
tR	Clock Rise Time		3		3		3	ns
tr	Clock Fall Time	_	3		3		3	ns
tsa	Address Setup Time	3.5		4		4	—	ns
tha	Address Hold Time	0		0		1	—	ns
tsc	Chip Enable Setup Time	3.5		4		4	—	ns
tнc	Chip Enable Hold Time	0		0		1		ns
tsв	Byte Enable Setup Time	3.5		4		4	—	ns
tнв	Byte Enable Hold Time	0		0		1	—	ns
tsw	R/W Setup Time	3.5		4		4		ns
tHW	R/W Hold Time	0		0		1	—	ns
tsp	Input Data Setup Time	3.5		4		4	—	ns
thd	Input Data Hold Time	0		0		1	—	ns
tsad	ADS Setup Time	3.5		4		4	—	ns
thad	ADS Hold Time	0		0		1	—	ns
tscn	CNTEN Setup Time	3.5		4		4	—	ns
then	CNTEN Hold Time	0		0		1		ns
t SRST	CNTRST Setup Time	3.5		4		4	—	ns
thrst	CNTRST Hold Time	0		0		1		ns
toe	Output Enable to Data Valid		6.5		7.5		9	ns
tolz	Output Enable to Output Low-Z ⁽¹⁾	2		2		2	—	ns
tонz	Output Enable to Output High-Z ⁽¹⁾	1	7	1	7	1	7	ns
tCD1	Clock to Data Valid (Flow-Through) ⁽²⁾		15		18		20	ns
tCD2	Clock to Data Valid (Pipelined) ⁽²⁾		6.5		7.5		9	ns
tDC	Data Output Hold After Clock High	2		2		2	—	ns
tскнz	Clock High to Output High-Z ⁽¹⁾	2	9	2	9	2	9	ns
tск⊥z	Clock High to Output Low-Z ⁽¹⁾	2		2		2	—	ns
Port-to-Port I	Delay	ł	•	•	•	•	-	-
tcwdd	Write Port Clock High to Read Data Delay		24		28		35	ns
tocs	Clock-to-Clock Setup Time	_	9		10		15	ns

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2). This parameter is guaranteed by device characterization, but is not production tested.

2. The Pipelined output parameters (tcvc2, tcb2) apply to either or both the Left and Right ports when FT/PIPE = VIH. Flow-through parameters (tcvc1, tcb1) apply when FT/PIPE = VIL for that port.

3. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE), FT/PIPER, and FT/PIPEL.

High-Speed 3.3V 8/4K x 18 Dual-Port Synchronous Pipelined Static RAM

Timing Waveform of Read Cycle for Flow-Through Output $(FT/PIPE"x" = VIL)^{(3,7)}$



Timing Waveform of Read Cycle for Pipelined Operation $(FT/PIPE"x" = VIH)^{(3,7)}$



- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. OE is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 3. $\overline{ADS} = VIL$ and $\overline{CNTRST} = VIH$.
- 4. The output is disabled (High-Impedance state) by $\overline{CE}_0 = V_{IH}$, $CE_1 = V_{IL}$ following the next rising edge of the clock. Refer to Truth Table 1.
- 5. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers
- are for reference use only. 6. If \overline{UB} or \overline{LB} was HIGH, then the Upper Byte and/or Lower Byte of DATAout for Qn + 2 would be disabled (High-Impedance state).
- 7. "X' here denotes Left or Right port. The diagram is with respect to that port.

Timing Waveform of a Bank Select Pipelined Read^(1,2)



Timing Waveform with Port-to-Port Flow-Through Read^(4,5,7)



- 1. B1 Represents Bank #1; B2 Represents Bank #2. Each Bank consists of one IDT70V9359/49 for this waveform, and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. \overline{UB} , \overline{LB} , \overline{OE} , and \overline{ADS} = VIL; CE1(B1), CE1(B2), R/W and \overline{CNTRST} = VIH.
- 3. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 4. \overline{CE}_{0} , \overline{UB} , \overline{LB} , and $\overline{ADS} = V_{1L}$; CE1 and $\overline{CNTRST} = V_{1H}$.
- 5. \overline{OE} = V_{IL} for the Right Port, which is being read from. \overline{OE} = V_{IH} for the Left Port, which is being written to.
- 6. If tccs ≤ maximum specified, then data from right port READ is not valid until the maximum specified for tcwpp.
- If tccs > maximum specified, then data from right port READ is not valid until tccs + tcp1. tcwbb does not apply in this case.
- 7. All timing is the same for both Left and Right ports. Port "A" may be either Left or Right port. Port "B" is the opposite from Port "A".

Timing Waveform of Pipelined Read-to-Write-to-Read ($\overline{OE} = VIL$)⁽³⁾



Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** Controlled)⁽³⁾



- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. CEo, UB, LB, and ADS = VIL; CE1 and CNTRST = VIH. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Flow-Through Read-to-Write-to-Read ($\overline{OE} = VIL$)⁽³⁾



Timing Waveform of Flow-Through Read-to-Write-to-Read (**OE** Controlled)⁽³⁾



- 1. Transition is measured 0mV from Low or High-impedance voltage with the Output Test Load (Figure 2).
- 2. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 3. \overline{CE}_{0} , \overline{UB} , \overline{LB} , and \overline{ADS} = VIL; \overline{CE}_{1} and \overline{CNTRST} = VIH. "NOP" is "No Operation".
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be re-written to guarantee data integrity.

Timing Waveform of Pipelined Read with Address Counter Advance⁽¹⁾



Timing Waveform of Flow-Through Read with Address Counter Advance⁽¹⁾



^{1.} \overline{CE}_{0} , \overline{OE} , \overline{UB} , and \overline{LB} = VIL; CE1, R/W, and \overline{CNTRST} = VIH.

^{2.} If there is no address change via ADS = VIL (loading a new address) or CNTEN = VIL (advancing the address), i.e. ADS = VIH and CNTEN = VIH, then the data output remains constant for subsequent clocks.

Timing Waveform of Write with Address Counter Advance (Flow-Through or Pipelined Outputs)⁽¹⁾



Timing Waveform of Counter Reset (Pipelined Outputs)⁽²⁾



- 1. \overline{CE}_0 , \overline{UB} , \overline{LB} , and $R/\overline{W} = V_{1L}$; CE_1 and $\overline{CNTRST} = V_{1H}$.
- 2. \overline{CE}_{0} , \overline{UB} , \overline{LB} = VIL; CE1 = VIH.
- 3. The "Internal Address" is equal to the "External Address" when ADS = VIL and equals the counter output when ADS = VIH.
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset cycle. ADDRo will be accessed. Extra cycles are shown here simply for clarification.
- 7. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1' Address is written to during this cycle.

High-Speed 3.3V 8/4K x 18 Dual-Port Synchronous Pipelined Static RAM

Functional Description

The IDT70V9359/49 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

 $\overline{CE}_0 = VIL$ and $CE_1 = VIH$ for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70V9359/49's for depth expansion configurations. When the Pipelined output mode is enabled, two cycles are required with $\overline{CE}_0 = VIL$ and $CE_1 = VIH$ to re-activate the outputs.

Depth and Width Expansion

The IDT70V9359/49 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the varioius chip enables in order to expand two devices in depth.

The IDT70V9359/49 can also be used in applications requiring expanded width, as indicated in Figure 4. Since the banks are allocated at the discretion of the user, the external controller can be set up to drive the input signals for the various devices as required to allow for 36-bit or wider applications.



NOTE:

1. A13 is for IDT70V9359, A12 is for IDT70V9349.

High-Speed 3.3V 8/4K x 18 Dual-Port Synchronous Pipelined Static RAM

Ordering Information



NOTE:

1. Contact your local sales office for Industrial temp range for other speeds, packages and powers.

2. Green parts available. For specific speeds, packages and powers contact your sales office.

LEAD FINISH (SnPb) parts are in EOL process. Product Discontinuation Notice - PDN# SP-17-02

IDT Clock Solution for IDT70V9359/49 Dual-Port

IDT Dual-Port Part Number	Dual-Port I/O Specitications		Clock Specifications				IDT	IDT
	Voltage	I/O	Input Capacitance	Input Duty Cycle Requirement	Maximum Frequency	Jitter Tolerance	PLL Clock Device	Non-PLL Clock Device
70V9359/49	3.3	LVTTL	9pF	40%	100	150ps	IDT2305 IDT2308 IDT2309	FCT3805 FCT3805D/E FCT3807 FCT3807D/E

5638 tbl 12

Industrial and Commercial Temperature Ranges

Datasheet Document History

10/01/01:		Initial Public Release
07/03/02:	Pages 2 & 3	Added data revision for pin configurations
		Consolidated multiple devices into one datasheet
08/15/03:		Removed Preliminary status
	Page 16	Added IDT Clock Solution Table
01/29/09:	Page 16	Removed "IDT" from orderable part number
07/26/10:	Page 1	Added green parts availability to features
	Page 16	Added green indicator to ordering information
	Page 8	In order to correct the header notes of the AC Elect Chars Table and align them with the Industrial temp range
	Dama 0 10	values located in the table, the commercial TA header note has been removed
	Pages 9-12	In order to correct the footnotes of timing diagrams, CNTEN has been removed to reconcile the footnotes with
00/00/40		the CNTEN logic definition found in Truth Table II - Address Counter Control
03/02/18:		Product Discontinuation Notice - PDN# SP-17-02 Last time buy expires June 15, 2018
03/06/20:		Datasheet changed to Obsolete Status
		·····



CORPORATE HEADQUARTERS 6024 Silver Creek Valley Road San Jose, CA 95138

for SALES: 800-345-7015 or 408-284-8200 fax: 408-284-2775 www.idt.com

for Tech Support: 408-284-2794 DualPortHelp@idt.com

The IDT logo is a registered trademark of Integrated Device Technology, Inc.